

Abstract of the Disclosure

A method for fabricating a capacitor in a semiconductor device is disclosed. The method comprises the steps of:

5 forming an interlayer insulating film on a semiconductor substrate, which includes a first contact hole exposing a certain portion of the substrate; forming a storage node plug filling the first contact hole; forming a first insulating film, a first silicon nitride film, and a second

10 insulating film sequentially above the substrate inclusive of the storage node plug; forming a second contact hole that exposes the storage node plug by removing the second insulating film, the first silicon nitride film, and the first insulating film partly; forming a recessed portion at

15 side surfaces of the second contact hole by wet-etching the first insulating film remained in the second contact hole; forming a storage node electrode of the capacitor, which is connected to the storage node plug, by filling the second contact hole inclusive of the recessed portion; removing the

20 remained second insulating film; and forming a dielectric film and a plate electrode sequentially on the entire surface of the storage node electrode structure.